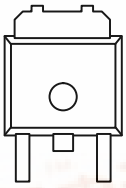
# N-Channel 30-V (D-S), 175°C, MOSFET PWM Optimized

**175°C Rated Maximum Junction Temperature TrenchFET® Power MOSFETs**

| PRODUCT SUMMARY | | |
|---|---|---|
| $V_{(BR)DSS}$ (V) | $r_{DS(on)}$ (Ω) | $I_D$ (A)[a] |
| 30 | 0.010 @ $V_{GS}$ = 10 V | 20 |
| | 0.014 @ $V_{GS}$ = 4.5 V | 18 |

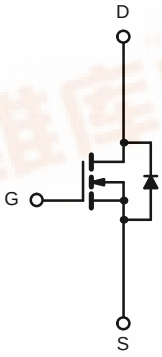
**TO-252**




Top View

Drain Connected to Tab

Order Number:
SUD50N03-10AP




N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS ($T_A$ = 25°C UNLESS OTHERWISE NOTED) | | | | |
|---|---|---|---|---|
| Parameter | | Symbol | Limit | Unit |
| Drain-Source Voltage | | $V_{DS}$ | 30 | V |
| Gate-Source Voltage | | $V_{GS}$ | ±20 | |
| Continuous Drain Current ($T_J$ = 175°C)[a] | $T_A$ = 25°C | $I_D$ | 20 | A |
| | $T_A$ = 100°C | | 14 | |
| Pulsed Drain Current | | $I_{DM}$ | 100 | |
| Continuous Source Current (Diode Conduction)[a] | | $I_S$ | 20 | |
| Maximum Power Dissipation | $T_C$ = 25°C | $P_D$ | 71[b] | W |
| | $T_A$ = 25°C | | 8.3[a] | |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | –55 to 175 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|---|---|---|---|---|---|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Maximum Junction-to-Ambient[a] | t ≤ 10 sec | $R_{thJA}$ | 15 | 18 | °C/W |
| | Steady State | | 40 | 50 | |
| Maximum Junction-to-Case | Steady State | $R_{thJC}$ | 1.75 | 2.1 | |

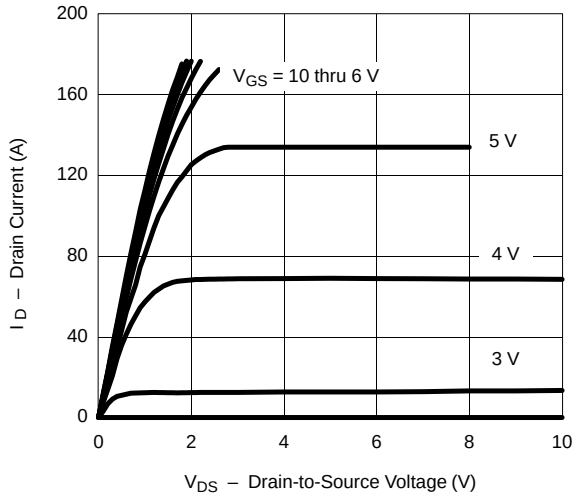
Notes:
a. Surface mounted on 1" x 1" FR4 Board, t ≤ 10 sec.
b. See SOA curve for voltage derating.

| MOSFET SPECIFICATIONS ($T_J$ =25°C UNLESS OTHERWISE NOTED) | | | | | | |
|---|---|---|---|---|---|---|
| **Parameter** | **Symbol** | **Test Condition** | **Min** | **Typ** | **Max** | **Unit** |
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 μA | 30 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_{DS}$ = 250 μA | 1 | 2 | | |
| Gate-Body Leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ±20 V | | | ±100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 30 V, $V_{GS}$ = 0 V | | | 1 | μA |
| | | $V_{DS}$ = 30 V, $V_{GS}$ = 0 V, $T_J$ = 125°C | | | 50 | |
| | | $V_{DS}$ = 30 V, $V_{GS}$ = 0 V, $T_J$ = 175°C | | | 150 | |
| On-State Drain Current[a] | $I_{D(on)}$ | $V_{DS}$ = 5 V, $V_{GS}$ = 10 V | 50 | | | A |
| Drain-Source On-State Resistance[a] | $r_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 15 A | | 0.0075 | 0.010 | Ω |
| | | $V_{GS}$ = 10 V, $I_D$ = 15 A, $T_J$ = 125°C | | | 0.016 | |
| | | $V_{GS}$ = 10 V, $I_D$ = 15 A, $T_J$ = 175°C | | | 0.019 | |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 15 A | | 0.011 | 0.014 | |
| Forward Transconductance[a] | $g_{fs}$ | $V_{DS}$ = 15 V, $I_D$ = 15 A | 20 | | | S |
| **Dynamic[b]** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 25 V, f = 1 MHz | | 2710 | 6000 | pF |
| Output Capacitance | $C_{oss}$ | | | 500 | | |
| Reversen Transfer Capacitance | $C_{rss}$ | | | 250 | | |
| Total Gate Charge[c] | $Q_g$ | $V_{DS}$ = 15 V, $V_{GS}$ = 10 V, $I_D$ = 20 A | | 55 | 100 | nC |
| Gate-Source Charge[c] | $Q_{gs}$ | | | 10 | | |
| Gate-Drain Charge[c] | $Q_{gd}$ | | | 9 | | |
| Turn-On Delay Time[c] | $t_{d(on)}$ | $V_{DD}$ = 15 V, $R_L$ = 0.3 Ω<br>$I_D$ ≃ 20 A, $V_{GEN}$ = 10 V, $R_G$ = 2.5 Ω | | 16 | 30 | ns |
| Rise Time[c] | $t_r$ | | | 90 | 135 | |
| Turn-Off Delay Time[c] | $t_{d(off)}$ | | | 33 | 60 | |
| Fall Time[c] | $t_f$ | | | 20 | 40 | |
| **Source-Drain Diode Ratings and Characteristics ($T_C$ = 25°C)[b]** | | | | | | |
| Continuous Current | $I_S$ | | | | 20 | A |
| Pulsed Current | $I_{SM}$ | | | | 100 | |
| Forward Voltage[a] | $V_{SD}$ | $I_F$ = 100 A, $V_{GS}$ = 0 V | | 1.2 | 1.5 | V |
| Reverse Recovery Time | $t_{rr}$ | $I_F$ = 20 A, di/dt = 100 A/μs | | 55 | 100 | ns |

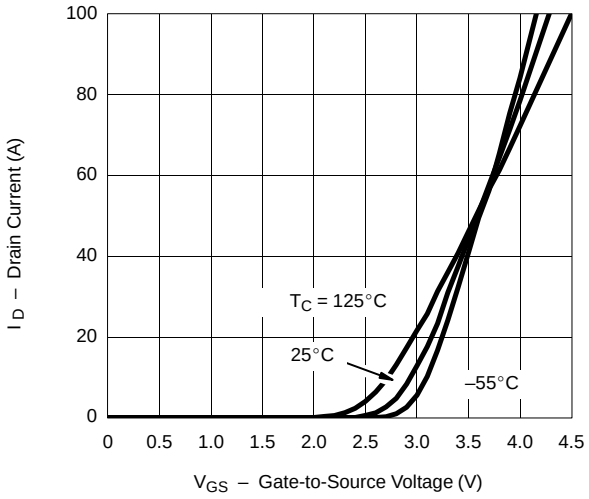
Notes:
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

## TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

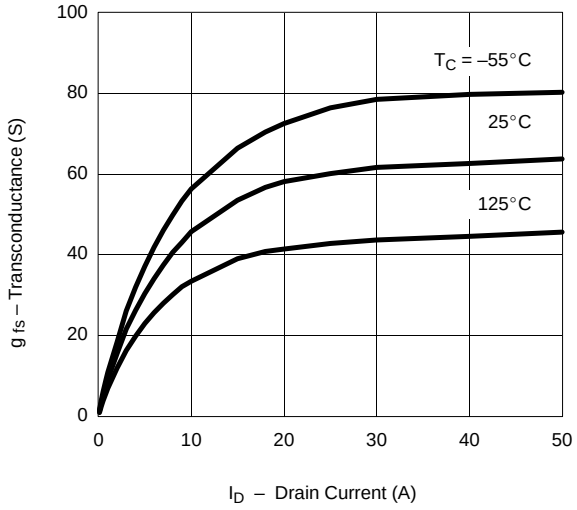
**Output Characteristics**



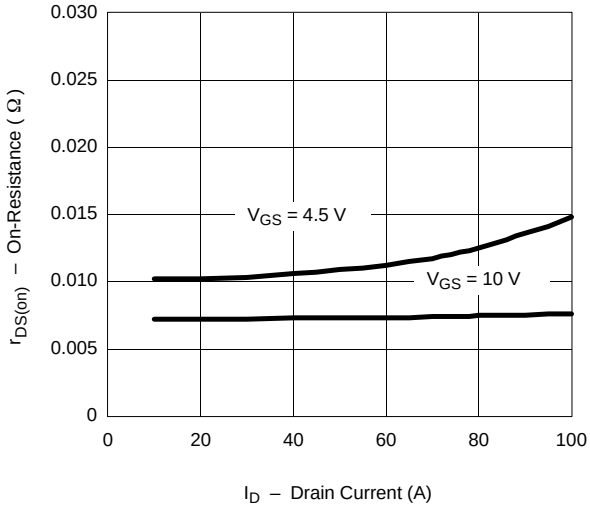

**Transfer Characteristics**



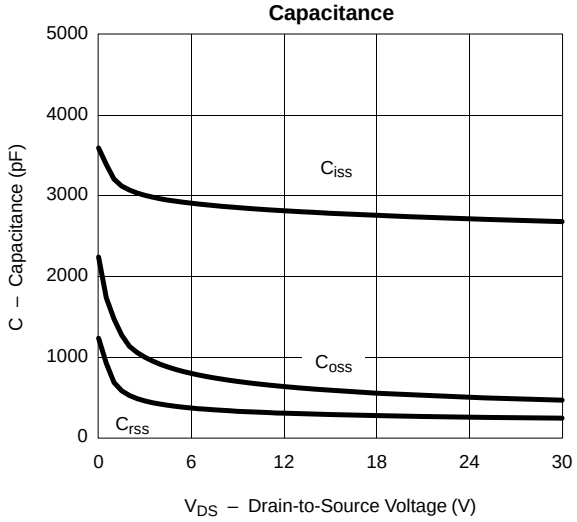

**Transconductance**



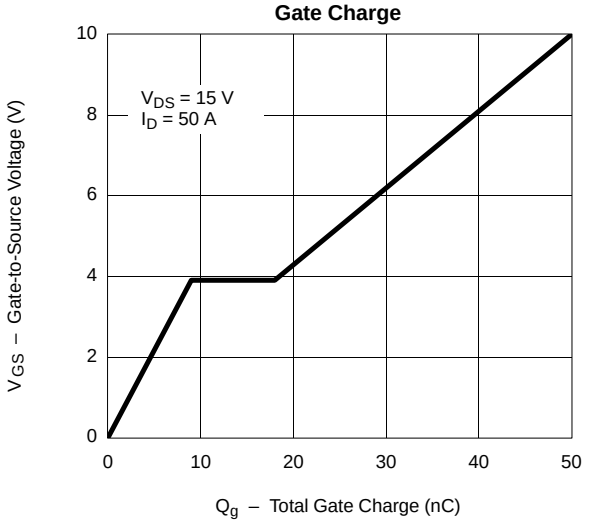

**On-Resistance vs. Drain Current**




**Capacitance**

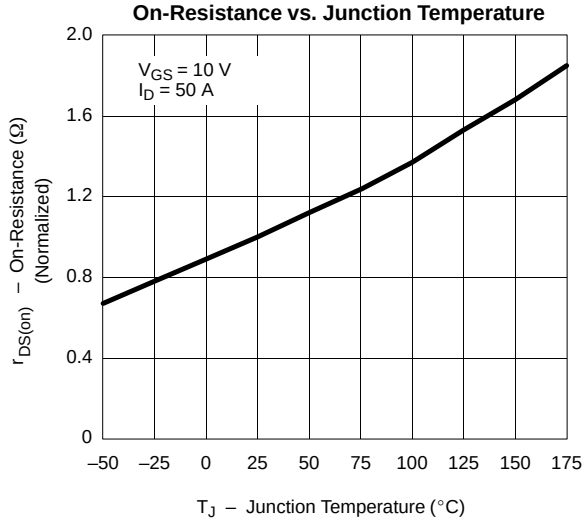



**Gate Charge**

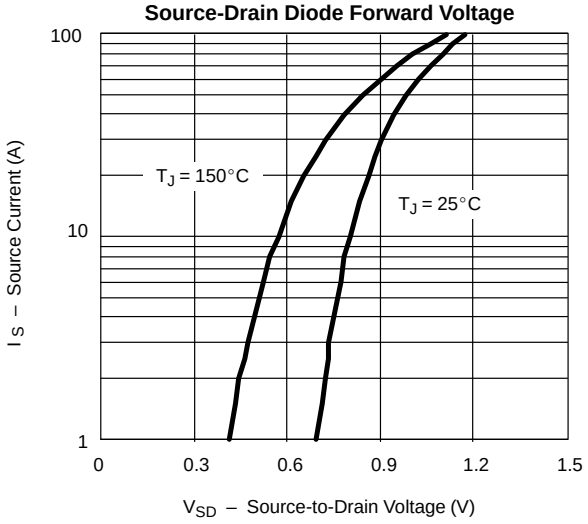


## TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

**On-Resistance vs. Junction Temperature**

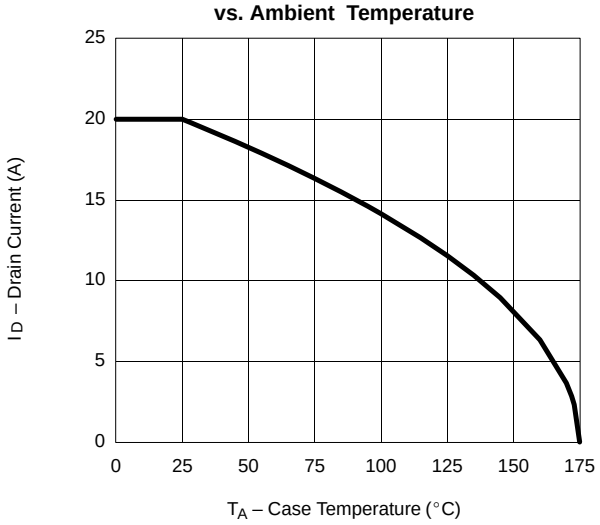



**Source-Drain Diode Forward Voltage**

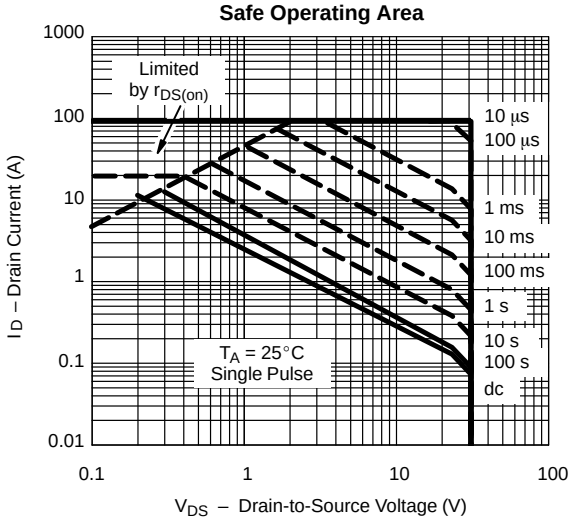



## THERMAL RATINGS

**Maximum Avalanche Drain Current vs. Ambient Temperature**




**Safe Operating Area**




**Normalized Thermal Transient Impedance, Junction-to-Ambient**